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润奥电子（扬州）制造有限公司

Y5SDD09D6000

High Voltage Diode

Properties

- Low forward voltage drop
- Low recovery charge
- High operating temperature
- Low leakage current

Key Parameters

V_{RRM}	=	6 000	V
I_{FAVm}	=	845	A
I_{FSM}	=	11 000	A
V_{TO}	=	0.893	V
r_T	=	0.647	mΩ

Applications

- Rectifier bridges

Types

	V_{RRM}
Y5SDD 09D6000	6 000 V
Conditions: $T_j = -40 + 150\text{ }^\circ\text{C}$, half sine waveform, $f = 50\text{ Hz}$	

Mechanical Data

F_m	Mounting force	$10 \pm 2\text{ kN}$
m	Weight	0.27 kg
D_s	Surface creepage distance	30 mm
D_a	Air strike distance	20 mm

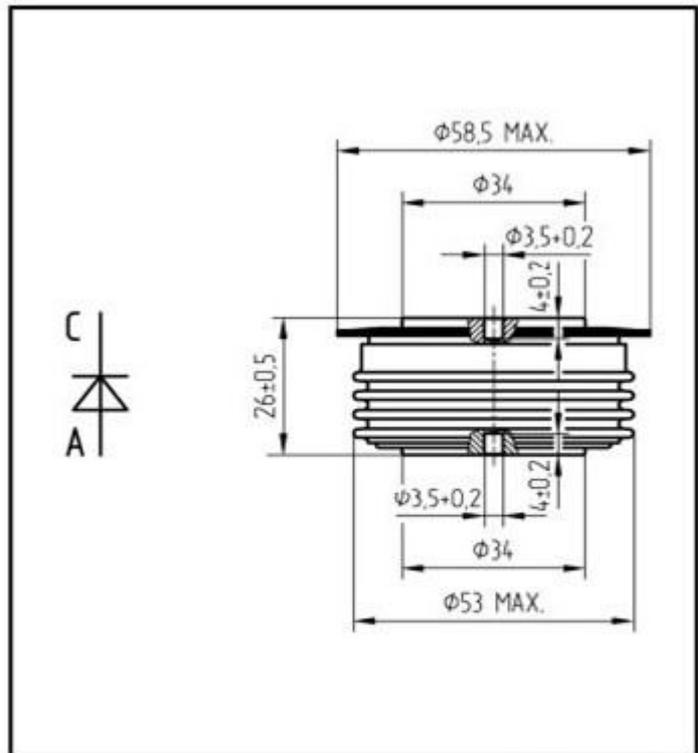


Fig. 1 Case

Maximum Ratings		Maximum Limits	Unit	
V_{RRM}	Repetitive peak reverse voltage $T_j = -40 + 150\text{ }^\circ\text{C}$	6 000	V	
I_{FAVM}	Average forward current $T_c = 85\text{ }^\circ\text{C}$	845	A	
I_{FRMS}	RMS forward current $T_c = 85\text{ }^\circ\text{C}$	1 328	A	
I_{RRM}	Repetitive reverse current $V_R = V_{RRM}$	50	mA	
I_{FSM}	Non repetitive peak surge current $V_R = 0\text{ V, half sine pulse}$	$t_p = 8.3\text{ ms}$	11 750	A
		$t_p = 10\text{ ms}$	11 000	A
I^2t	Limiting load integral $V_R = 0\text{ V, half sine pulse}$	$t_p = 8.3\text{ ms}$	573 000	A ² s
		$t_p = 10\text{ ms}$	605 000	A ² s
$T_{jmin} - T_{jmax}$	Operating temperature range	-40 ÷ 150	°C	
T_{STG}	Storage temperature range	-40 ÷ 150	°C	

Unless otherwise specified $T_j = 150\text{ }^\circ\text{C}$

Characteristics		Value			Unit
		<i>min</i>	<i>typ</i>	<i>max</i>	
V_{T0}	Threshold voltage			0.893	V
r_T	Forward slope resistance $I_{F1} = 1\ 335\text{ A, } I_{F2} = 4\ 006\text{ A}$			0.647	mΩ
V_{FM}	Maximum forward voltage $I_{FM} = 1\ 500\text{ A}$			1.870	V
Q_{rr}	Recovered charge $V_R = 100\text{ V, } I_{FM} = 1\ 000\text{ A, } di/dt = -30\text{ A}/\mu\text{s}$		3 600		μC

Unless otherwise specified $T_j = 150\text{ }^\circ\text{C}$

Thermal Parameters			Value	Unit
R_{thjc}	Thermal resistance junction to case	double side cooling	32	K/kW
		anode side cooling	50	
		cathode side cooling	88	
R_{thch}	Thermal resistance case to heatsink	double side cooling	8	K/kW
		single side cooling	16	

Transient Thermal Impedance

Analytical function for transient thermal impedance

$$Z_{thjc} = \sum_{i=1}^5 R_i (1 - \exp(-t / \tau_i))$$

Conditions:
 $F_m = 10 \pm 2$ kN, Double side cooled

Correction for periodic waveforms

180° sine:	2.3 K/kW
180° rectangular:	3.1 K/kW
120° rectangular:	5.1 K/kW
60° rectangular:	8.7 K/kW

i	1	2	3	4	5
τ_i (s)	0.7033	0.2185	0.0588	0.0042	0.0006
R_i (K/kW)	11.56	10.08	7.84	2.38	0.13

Fig. 2 Dependence transient thermal impedance junction to case on square pulse

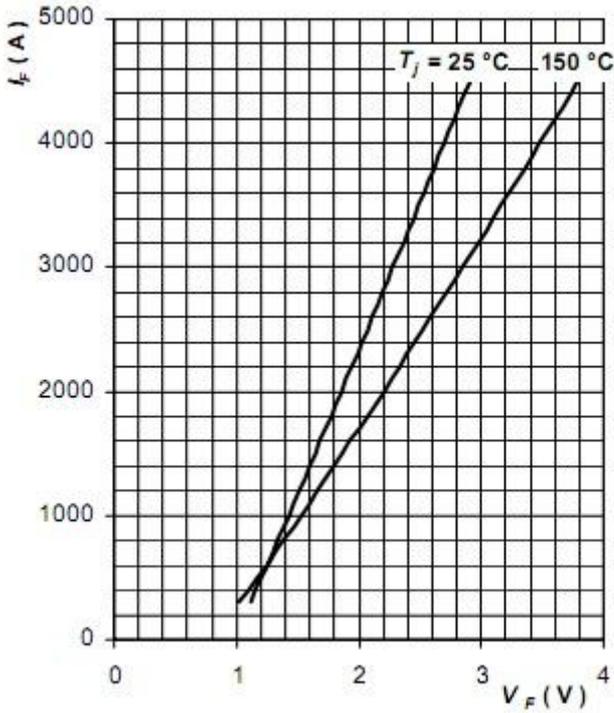


Fig. 3 Maximum forward voltage drop characteristics

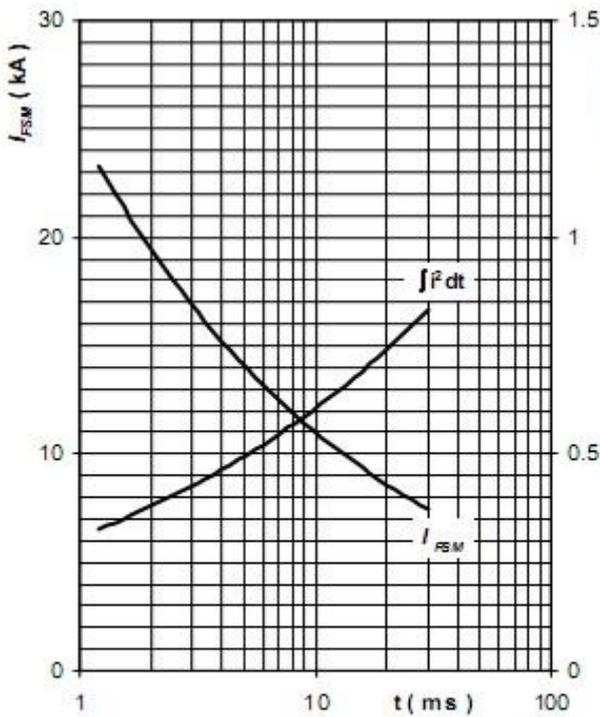


Fig. 4 Surge forward current vs. pulse length, half sine wave, single pulse, $T_J = T_{Jmax}$

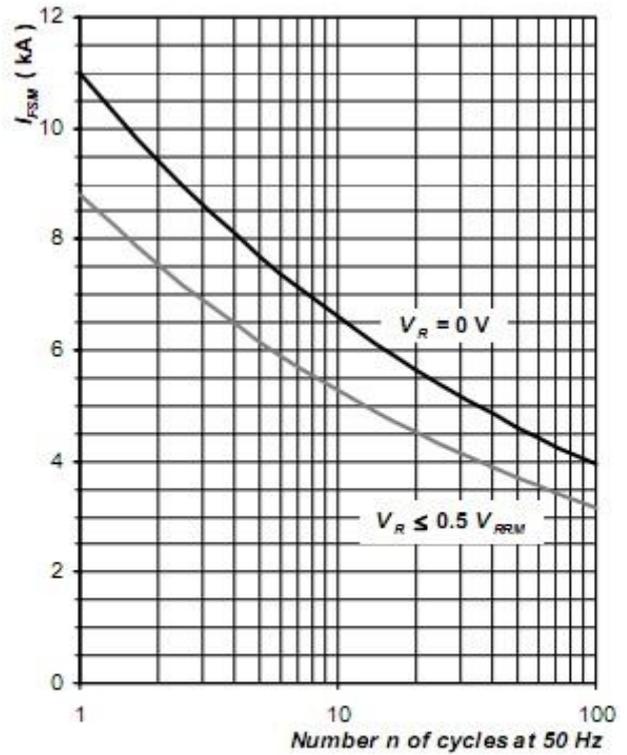


Fig. 5 Surge forward current vs. number of pulses, half sine wave, $T_J = T_{Jmax}$

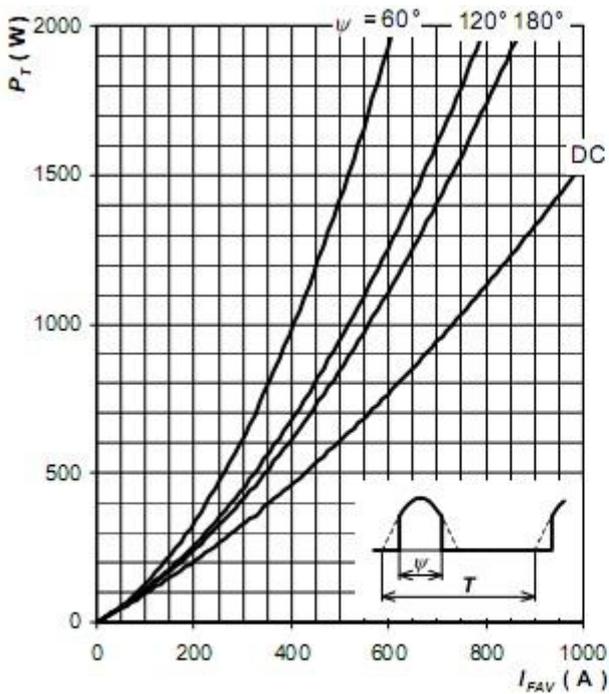


Fig. 6 Forward power loss vs. average forward current, sine waveform, $f = 50 \text{ Hz}$, $T = 1/f$

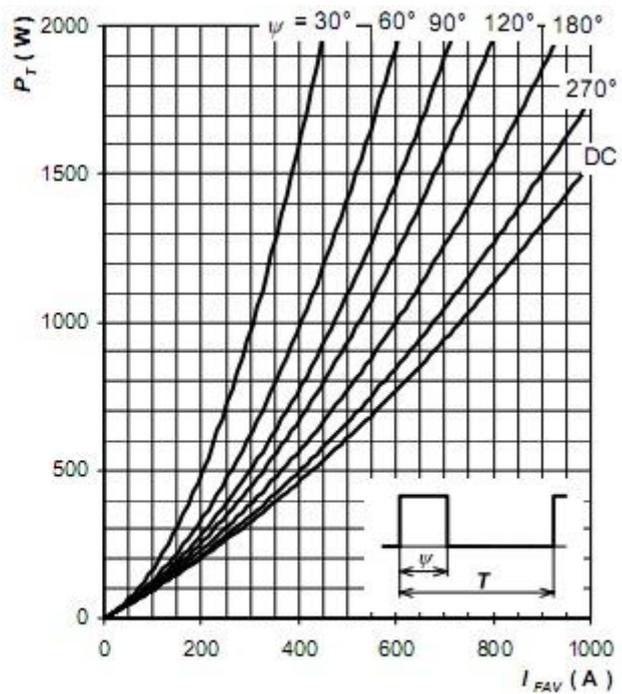


Fig. 7 Forward power loss vs. average forward current, square waveform, $f = 50 \text{ Hz}$, $T = 1/f$

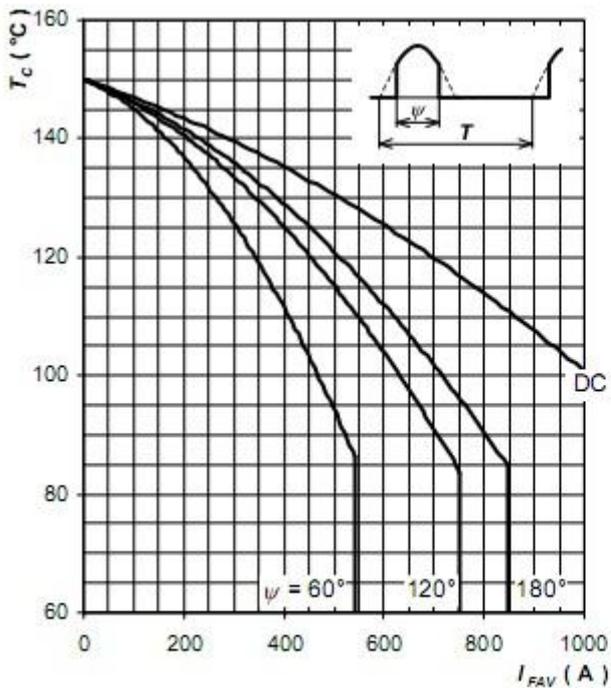


Fig. 8 Max. case temperature vs. aver. forward current, sine waveform, $f = 50 \text{ Hz}$, $T = 1/f$

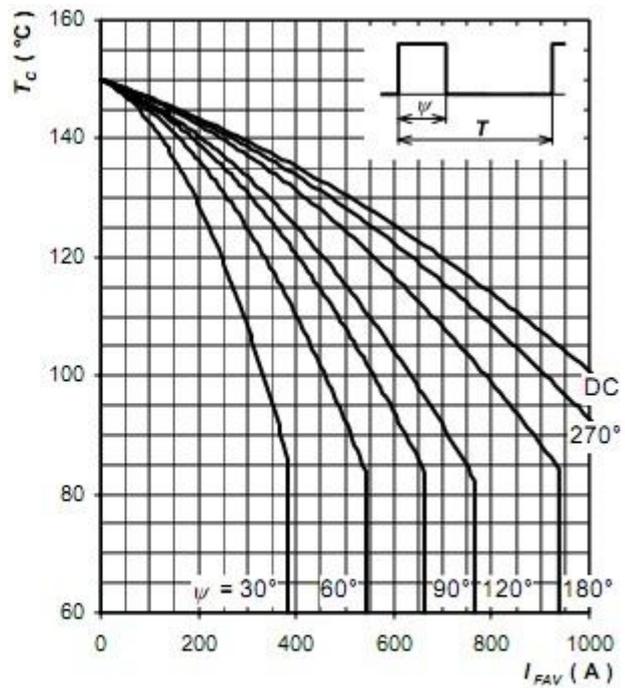


Fig. 9 Max. case temperature vs. aver. forward current, square waveform, $f = 50 \text{ Hz}$, $T = 1/f$